



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yeo, *et al.* Attorney Docket: TSM03-0553
Filed: September 22, 2003 Examiner: Unknown
Serial No.: 10/667,871 Art Unit: 2811
For: Resistor with Reduced Leakage

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A & 08B that may be considered material to the examination of the above-identified application.

Cites A-P are being filed under the waived requirement of 37 CFR 1.98(a)(2)(i) dated July 11, 2003; therefore, copies of these U.S. patents are not included. Cites Q-X, non-U.S. patents, are attached.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(1), within three months of the filing date of a national application other than a continued prosecution application under § 1.53(d).

Respectfully submitted,

Ira S. Matsil
Attorney for Applicant
Reg. No. 35,272

December 22, 2003

Date

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PTO/SB/08A (05-03)

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	10/667,871
Filing Date	September 22, 2003
First Named Inventor	Yeo, <i>et al.</i>
Art Unit	2811
Examiner Name	Unknown
Attorney Docket Number	TSM03-0553

Sheet 1 of 2

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
	A	US-4,314,269	02-02-1982	Fujiiki	
	B	US-5,629,544	05-13-1997	Voldman, <i>et al.</i>	
	C	US-5,811,857	09-22-1998	Assaderaght, <i>et al.</i>	
	D	US-6,008,095	12-28-1999	Gardner, <i>et al.</i>	
	E	US-6,015,993	01-18-2000	Voldman, <i>et al.</i>	
	F	US-6,232,163 B1	05-15-2001	Voldman, <i>et al.</i>	
	G	US-6,258,664 B1	07-10-2001	Reinberg	
	H	US-6,294,834 B1	09-25-2001	Yeh, <i>et al.</i>	
	I	US-6,358,791 B1	03-19-2002	Hsu, <i>et al.</i>	
	J	US-2002/0153549 A1	10-24-2002	Laibowitz, <i>et al.</i>	
	K	US-6,475,838 B1	11-05-2002	Bryant, <i>et al.</i>	
	L	US-6,489,664 B2	12-03-2002	Re, <i>et al.</i>	
	M	US-2003/0030091 A1	02-13-2003	Bulsara, <i>et al.</i>	
	N	US-6,524,905 B2	02-25-2003	Yamamichi, <i>et al.</i>	
	O	US-2003/0080386 A1	05-01-2003	Ker, <i>et al.</i>	
	P	US-6,558,998 B2	05-06-2003	Belleville, <i>et al.</i>	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
	Q	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	R	WANG, L.K., <i>et al.</i> , "On-Chip Decoupling Capacitor Design to Reduce Switching-Noise-Induced Instability in CMOS/SOI VLSI," Proceedings of the 1995 IEEE International SOI Conference, Oct. 1995, pp. 100-101.	
	S	YEOH, J.C., <i>et al.</i> , "MOS Gated Si:SiGe Quantum Wells Formed by Anodic Oxidation," Semicond. Sci. Technol. (1998), Vol. 13, pp. 1442-1445, IOP Publishing Ltd., UK.	
	T	CAVASSILAS, N., <i>et al.</i> , "Capacitance-Voltage Characteristics of Metal-Oxide-Strained Semiconductor Si/SiGe Heterostructures," Nanotech 2002, Vol. 1, pp. 600-603.	

Examiner
SignatureDate
Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO				Complete if Known	
				Application Number	10/667,871
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	September 22, 2003
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				Group Art Unit	2811
				Examiner Name	Unknown
				Attorney Docket Number	TSM03-0553
Sheet	2	of	2		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite, No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	U	BLAAUW, D., <i>et al.</i> , "Gate Oxide and Subthreshold Leakage Characterization, Analysis and Optimization," date unknown.	
	V	"Future Gate Stack," International Sematech, 2001 Annual Report.	
	W	CHANG, L., <i>et al.</i> , "Reduction of Direct-Tunneling Gate Leakage Current in Double-Gate and Ultra-Thin Body MOSFETs," 2001 IEEE, Berkeley, CA.	
	X	CHANG, L., <i>et al.</i> , "Direct-Tunneling Gate Leakage Current in Double-Gate and Ultrathin Body MOSFETs," 2002 IEEE, Vol. 49, No. 12, December 2002.	

Examiner Signature		Date Considered	
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